

#### North South University

#### Department of Electrical & Computer Engineering

# LAB REPORT Spring 2021

Course Code: EEE 111

Course Title: Analog Electronics - I

Section: 7

Experiment Number: 01

**Experiment Name:** 

I-V Characteristics of diode

Experiment Date: 02 / 03 / 2021

Date of Submission: 16 / 03 / 2021

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## LAB REPORT-OL

Name of experiment: 1-V Characteristics of diode

## Objective:

The objective of this experiment is to study the I-V Characteristics of diode

# Equipments and components:

| Social no. | Component Details  | Specification |                  |
|------------|--------------------|---------------|------------------|
| 1          | P-n junction diode | IN4007        | 1 piece          |
| 2          | Resistan           | Kn            | 1 piece          |
| 3          | DC POWER SUPPLY    |               | 1 unit           |
| 4          | signal generator   |               | 1 unit           |
| 5          | Toraineor Board    |               | 1 unit           |
| 6          | Oscilloscope       |               | 1 unit           |
| 7          | Digital Multimeter |               | 1 wit            |
| 8          | Chools and wite    |               | a s<br>oreawined |

## Theory

A diode is a bi-polar (one end is positive and another is negative). A diode can be in two states depending on the direction of powers. If a diode's positive end is connected to a power supplies positive end then it will be in Forward a biasing and behave as a short circuit. And if the diode's positive end is connected to the power supplies megative end then it'll be in supplies megative end then it'll be in one verse biasing and behave as a

#### Circuit D'iagram:

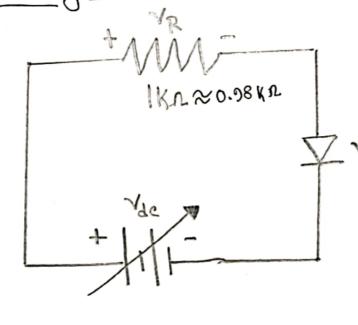


Fig: Cinemit Diagnam
of a forward
biasing diode

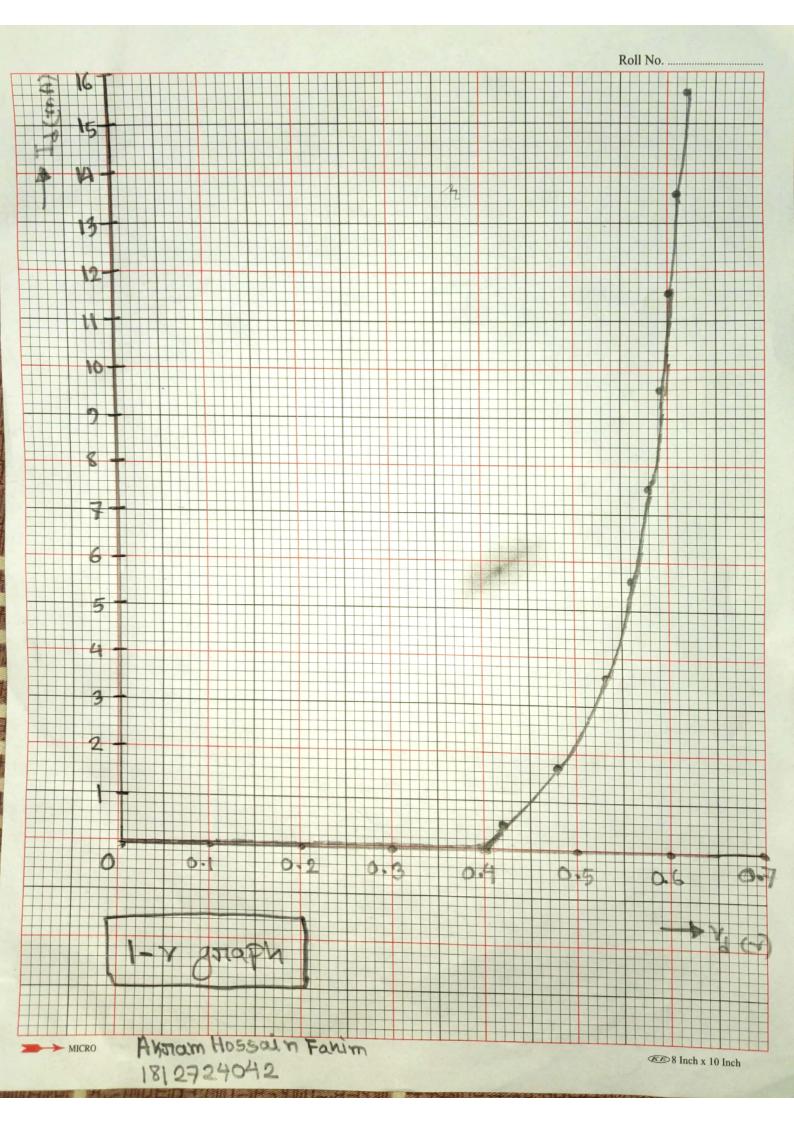
## Data Table 6

| q6 (A) | J, (A) | Y <sub>R (v)</sub> | Id = VR/R |
|--------|--------|--------------------|-----------|
| 0      | 0      | 0                  | 0         |
| 1      | 0.42   | 0.57               | 0.58      |
| 2      | 0.48   | 1.51               | 1.54      |
| 4      | 0.53   | 3.46               | 3.53      |
| 6      | 0.56   | 5.43               | 5.54      |
| 8      | 0.58   | 7.41               | 7.56      |
| 10     | 0.59   | 2.40               | ე. 6ე     |
| 12     | 0.60   | 11.39              | 11.62     |
| 14     | 0.61   | 13.38              | 13.65     |
| 16     | 0.62   | 15.37              | 15.68     |

### Questions:

(1) Donaw the L-V Characteristics Chare of diode forom the treading obtain in this experiment.

Ans: The graph of the curve has been attached with the lab report.



2) Calculate the static resistance For Id=5mA and Id = 10 mA.

for  $I_d = 5mA$ ,  $V_d$  is 0.55V. (From graph)  $R_d = \frac{0.55V}{5mA}$  = 110-2

$$R_{d} = \frac{0.557}{5mA}$$

Foor Id= 10 mA, Vd is 0.595 V (Forom graph)

$$R_{1} = \frac{0.595 \text{ V}}{10 \text{ mA}}$$

3 Determin the Q-point for the circuit in figure -6, when  $V_{le} = 8 \text{ volt}$ .

Ans:
From the data table we can see for 87614 Yde, Yd is 0.58 volts and Id is 7.56 mA.

50 the Q-Point is (0.58, 7.56)



## Discussions

In this experiment we learned about how a diode functions depending on the direction of powers. We have experimented with a forward biasing circuit to learn about the threshold voltage of the diode. which in this case was between 0.6 v-0.7 v. in this case was between 0.6 v-0.7 v. We have also simulated the circuit in multisim.

